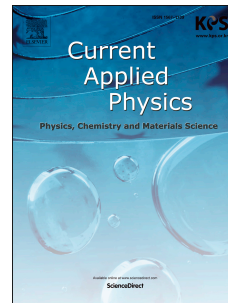


# Accepted Manuscript

Improved Schottky behavior of GaN nanorods using hydrogen plasma treatment

Maddaka Reddeppa, Byung-Guon Park, Sang-Tae Lee, Nguyen Hoang Hai, Moon-Deock Kim, Jae-Eung Oh



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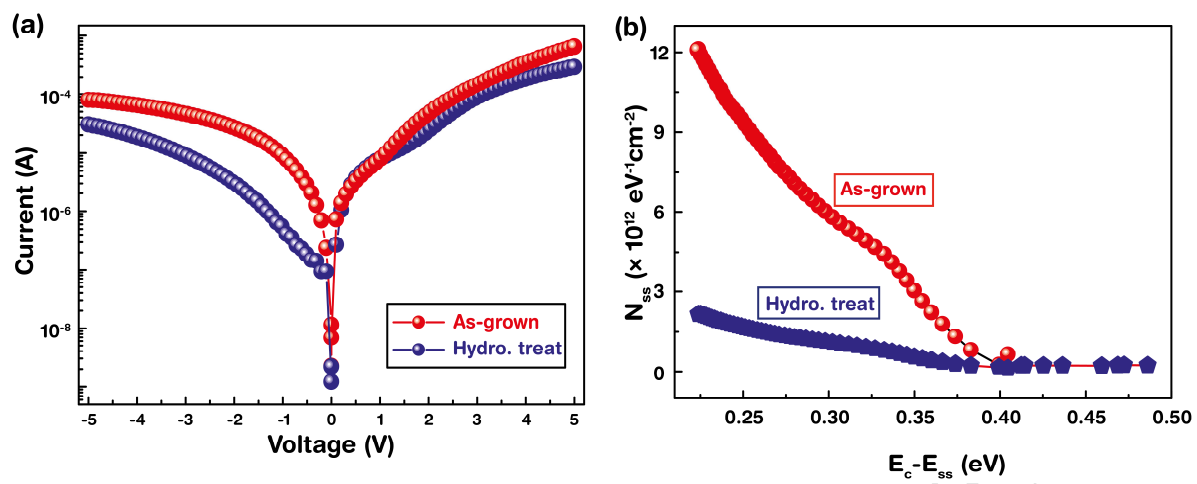
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